IDGN-3 Time table

Updated: Jan. 12, 2017

Time	Session
January 16, 2017	
18:00–19:00	Welcome Reception at Auditorium, Bldg. 2, IMR, Tohoku University

Time	Session		
January 17, 2017			
8:30–9:00	Registration		
9:00–9:10	Opening address		
9:10–11:30	Session I: Electronic Devices I	**Masaaki Kuzuhara** *Fukui University* *Japan*	Reduced current collase in AlGaN/GaN HEMTs for low-loss power switching operation
		Tetsuya Suemitsu *Tohoku University* *Japan*	Neutral beam etching: A new approach to minimize plasma-induced damages in GaN-based devices
		Jan Kuzmik *Slovak Academy of Sciences* *Slovakia*	GaN-based normally-off HEMTs for switching and logic applications
		Kiattiwut Prasertsuk *Tohoku University* *Japan*	MOVPE Growth of N-polar GaN/AlGaN/GaN Inverted HEMT Structures and Their Electrical Properties
11:30–13:00	Lunch Discussion		
13:00–14:10	Session II: Crystal growth of Bulk GaN	**Yohei Otoki** *SCIOCS* *Japan*	Development of high quality large size GaN substrates and improvement of GaN electrical devices performance by using GaN substrates
		Malgorzata Iwinska *UNIPRESS* *Poland*	HVPE as a method for crystallizing GaN with low background impurity concentration with controllable doping – highly conductive n-type and semi-indulating material
14:10–14:25	Coffee Break		
14:25–16:10	Session III: Growth of AlN and AlGaN	**Masayoshi Adachi** *Tohoku University* *Japan*	Liquid phase epitaxial growth of AlN layer on nitrided sapphire templates using Ga-Al solution
		Balaji Manavaimaran *University of Madras* *India*	Epitaxial growth of Aluminum Nitride for opto-electronic applications
		Venkatachalam Sabarinathan *Manonmaniam Sundaranar University* *India*	Growth of AlGaN for Deep UV applications
16:10–16:25	Coffee Break		

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16:25–18:10	Session IV: Characterization for Devices	**Osamu Ueda** *Kanazawa Inst. Tech.* *Japan*	Gradual degradation in III–V and GaN–related optical devices
		Akira Sakai *Osaka University* *Japan*	Structural characterization of defects in nitride semiconductor materials
		Yoshihiro Ishitani *Chiba University* *Japan*	Photonic phenomenon in carrier dynamics and interaction with radiation in III–nitride materials
19:00–21:00	Banquet at the Westin Sendai		

Time	Session		
January 18, 2017			
8:30–9:00	Registration		
9:00–9:10	Information		
9:10–11:30	Session V: Electronic Devices II	**Tsunenobu Kimoto** *Kyoto University* *Japan*	Progress and Future Challenges of High–Voltage SiC Power Devices
		Tamotsu Hashizume *Hokkaido University* *Japan*	Improved MOS gate control for GaN power transistors
		Shinya Takashima *Fuji Electoric co. ltd.* *Japan*	MOS channel properties on homoepitaxially–grown p–type GaN layers
		Tetsu Kachi *Nagoya University* *Japan*	GaN on GaN power devices –Present status of process technology–
11:30–11:45	Closing		